Schottky barrier diode
RB495D (tentative standards)

●Applications

Low current rectification (cathode common twin model)

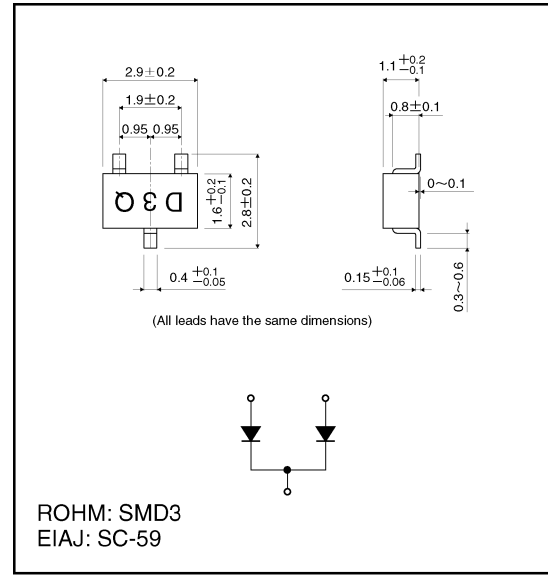
●Features

1) Compact mold model. (SMD3)
2) High reliability.
3) Two diodes with common cathode for excellent installation efficiency.

●Construction

Silicon epitaxial

●External dimensions (Units: mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	25	V
Mean rectifying current *1	I_O	0.4	A
Peak forward surge current *2	I_{FSM}	2	A
Junction temperature	Tj	125	℃
Storage temperature	Tstg	−40～125	℃
Operating temperature	Topr	−30～85	℃

*1 Mean output current per element: I_O / 2

*2 60Hz for 1 ∿

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_{F(1)}$	−	−	0.30	V	I_F=10mA
	$V_{F(2)}$	−	−	0.50	V	I_F=200mA
Reverse current	I_R	−	−	70	μA	V_R=25V

*ESD sensitive product handling required.

●Electrical characteristic curves (Ta = 25°C unless specified otherwise)

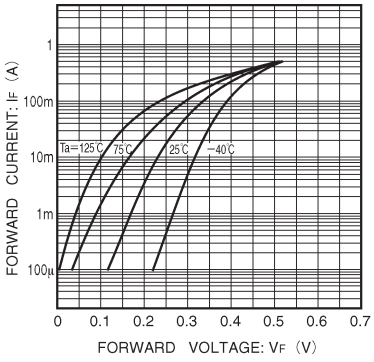


Fig. 1 Forward characteristics

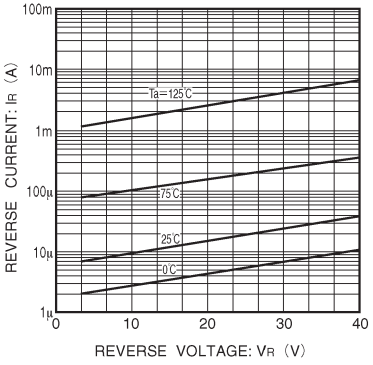


Fig. 2 Reverse characteristics

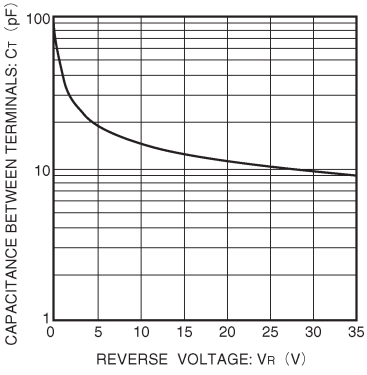


Fig. 3 Capacitance between terminals characteristics